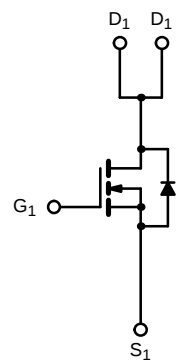
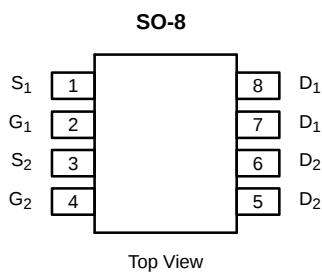


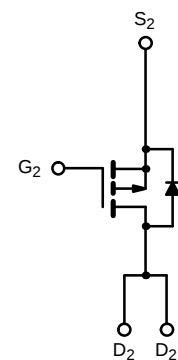


Complimentary 30-V (D-S) MOSFET

PRODUCT SUMMARY			
	V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
N-Channel	30	0.05 @ $V_{GS} = 10$ V	± 3.5
		0.07 @ $V_{GS} = 6$ V	± 3
		0.08 @ $V_{GS} = 4.5$ V	± 2.5
P-Channel	-30	0.10 @ $V_{GS} = -10$ V	± 3.5
		0.12 @ $V_{GS} = -6$ V	± 3
		0.16 @ $V_{GS} = -4.5$ V	± 2.5



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V _{DS}	30	−30	V
Gate-Source Voltage		V _{GS}	± 20	± 20	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	± 3.5	± 3.5	A
	T _A = 70 °C		± 2.8	± 2.8	
Pulsed Drain Current		I _{DM}	± 20	± 20	
Continuous Source Current (Diode Conduction) ^a		I _S	1.7	−1.7	
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	2.0		W
	T _A = 70 °C		1.3		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	−55 to 150		°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	N- or P- Channel	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	62.5	$^\circ\text{C/W}$

Notes

a. Surface Mounted on FR4 Board, $t \leq 10$ sec.

SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition		Min	Typ ^a	Max	Unit
Static							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	N-Ch	1.0			V
		V _{DS} = V _{GS} , I _D = −250 μA	P-Ch	−1.0			
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V				±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V	N-Ch			1	μA
		V _{DS} = −24 V, V _{GS} = 0 V	P-Ch			−1	
		V _{DS} = 15 V, V _{GS} = 0 V, T _J = 70°C	N-Ch			5	
		V _{DS} = −15 V, V _{GS} = 0 V, T _J = 70°C	P-Ch			−5	
On-State Drain Current ^b	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	N-Ch	20			A
		V _{DS} ≤ −5 V, V _{GS} = −10 V	P-Ch	−20			
		V _{DS} ≥ 5 V, V _{GS} = 4.5 V	N-Ch	3.5			
		V _{DS} ≤ −5 V, V _{GS} = −4.5 V	P-Ch	−3.5			
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 3.5 A	N-Ch		0.04	0.05	Ω
		V _{GS} = −10 V, I _D = 3.5 A	P-Ch		0.074	0.10	
		V _{GS} = 6 V, I _D = 3 A	N-Ch		0.045	0.07	
		V _{GS} = −6 V, I _D = 3 A	P-Ch		0.090	0.12	
		V _{GS} = 4.5 V, I _D = 2.5 A	N-Ch		0.054	0.08	
		V _{GS} = −4.5 V, I _D = 2 A	P-Ch		0.115	0.16	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 3.5 A	N-Ch		9		S
		V _{DS} = −15 V, I _D = −3.5 A	P-Ch		6		
Diode Forward Voltage ^b	V _{SD}	I _S = 1.7 A, V _{GS} = 0 V	N-Ch		0.75	1.2	V
		I _S = −1.7 A, V _{GS} = 0 V	P-Ch		−0.75	−1.2	
Dynamic ^a							
Total Gate Charge	Q _g	N-Channel V _{DS} = 10 V, V _{GS} = 10 V, I _D = 3.5 A P-Channel V _{DS} = −10 V, V _{GS} = −10 V I _D = −3.5 A	N-Ch		14	35	nC
			P-Ch		14.5	35	
Gate-Source Charge	Q _{gs}		N-Ch		1.9		
			P-Ch		2.7		
Gate-Drain Charge	Q _{gd}	N-Ch		2.8			
		P-Ch		3.5			
Turn-On Delay Time	t _{d(on)}	N-Channel V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω P-Channel V _{DD} = −15 V, R _L = 15 Ω I _D ≅ −1 A, V _{GEN} = −10 V, R _G = 6 Ω	N-Ch		10	30	ns
			P-Ch		11	30	
Rise Time	t _r		N-Ch		10	40	
			P-Ch		11	40	
Turn-Off Delay Time	t _{d(off)}		N-Ch		26	50	
			P-Ch		30	50	
Fall Time	t _f		N-Ch		10	50	
			P-Ch		12	50	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 3.5 A, di/dt = 100 A/μs	N-Ch		60	120	
			P-Ch		40	100	

Notes

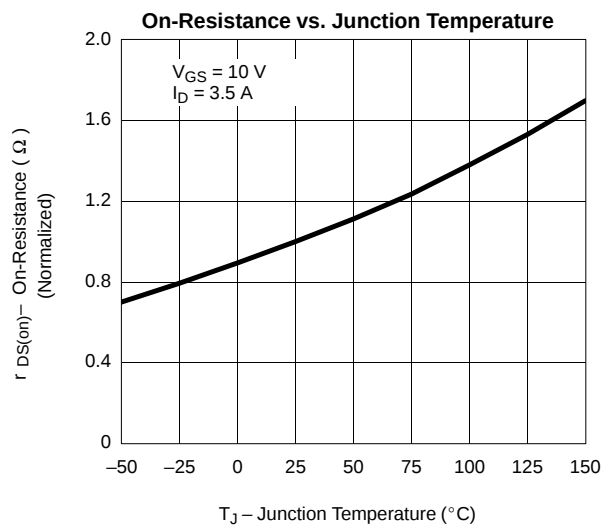
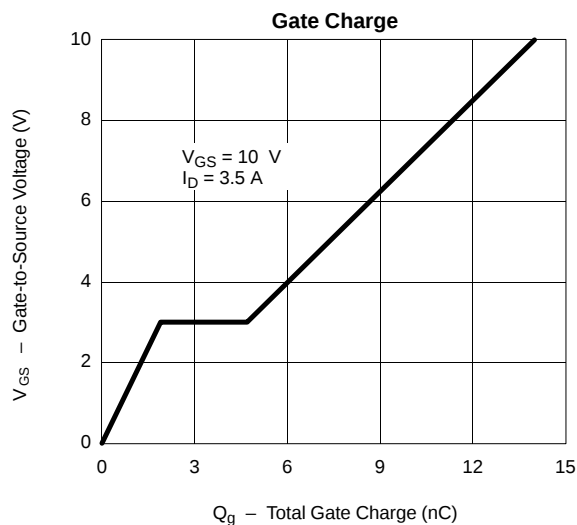
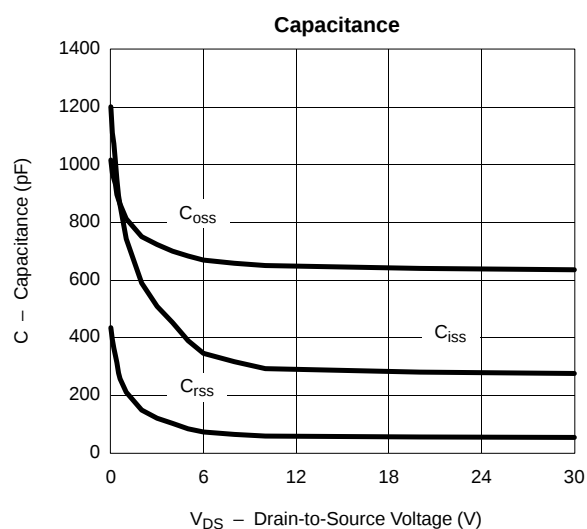
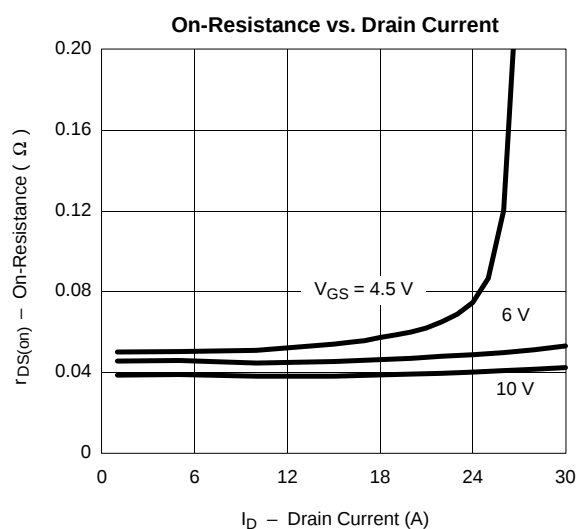
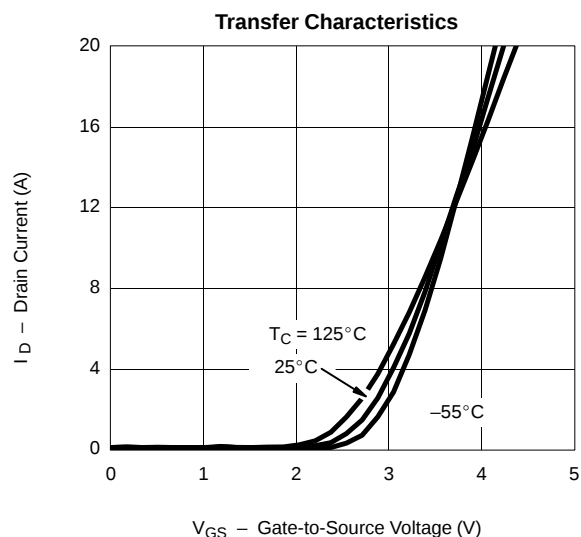
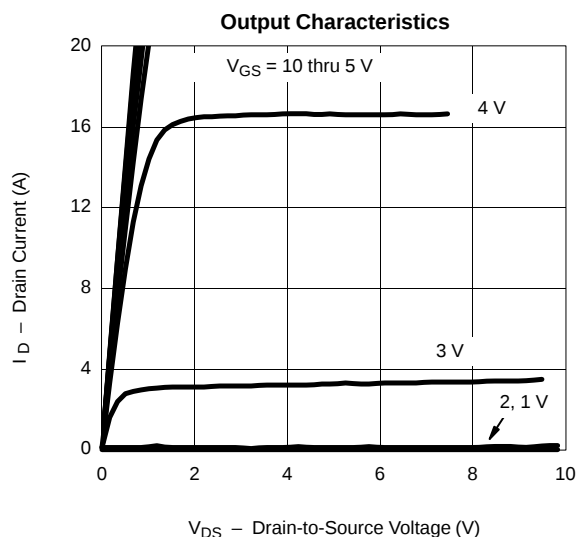
a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.



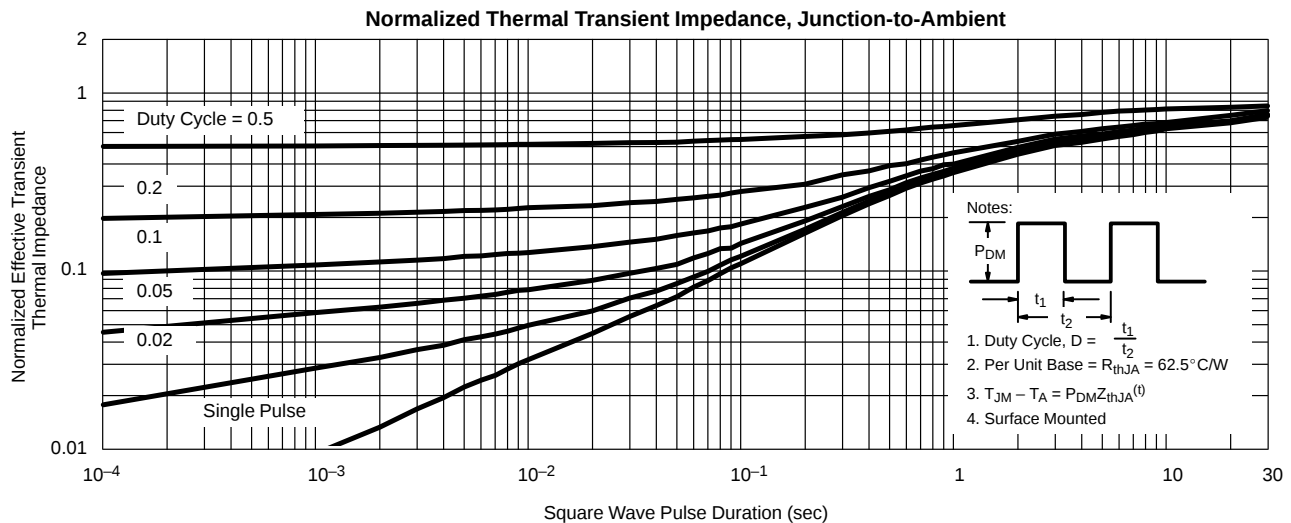
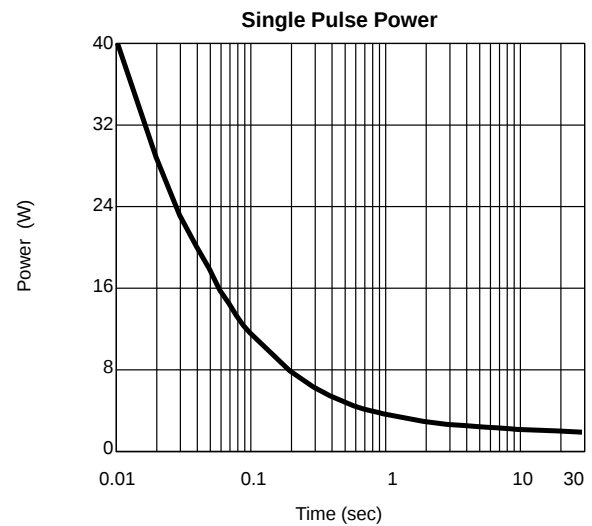
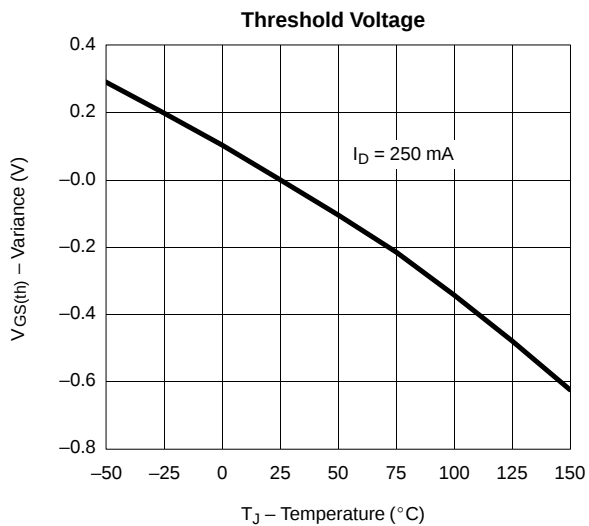
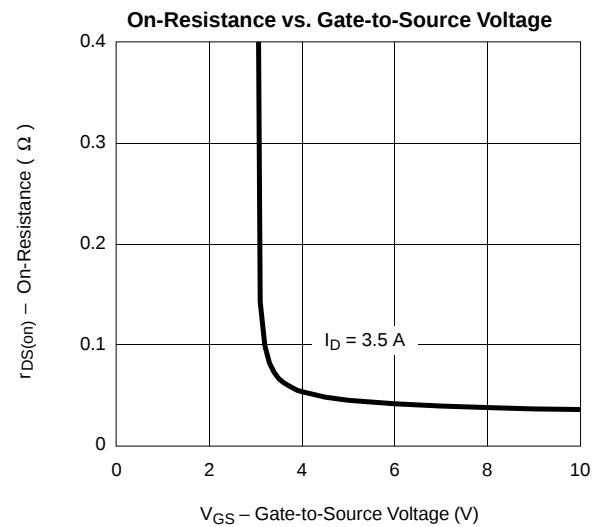
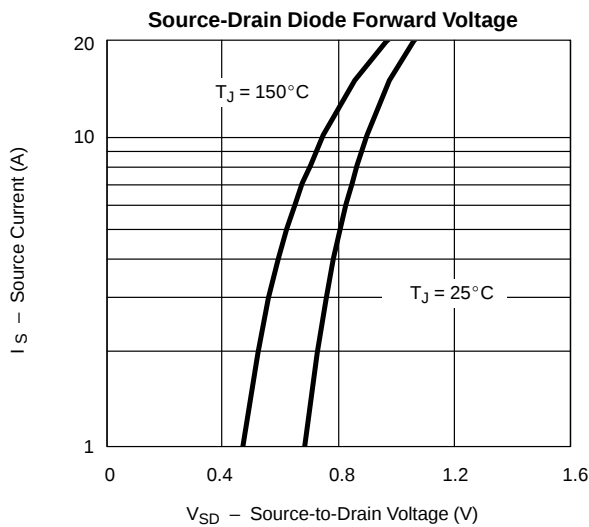
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

N-CHANNEL



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

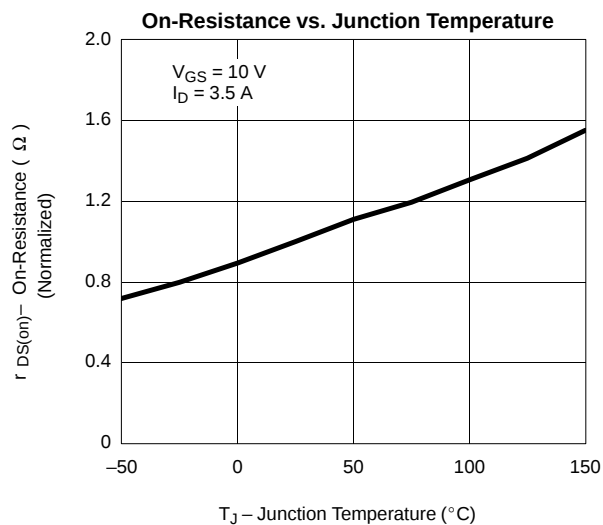
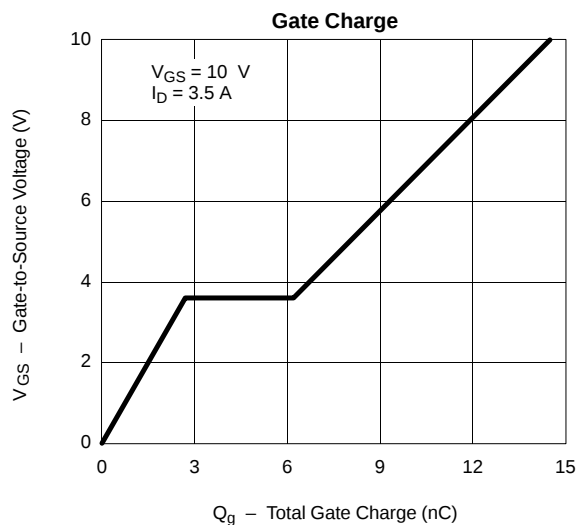
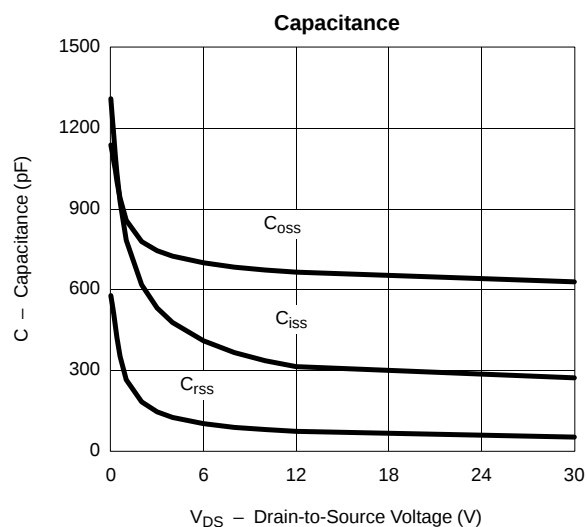
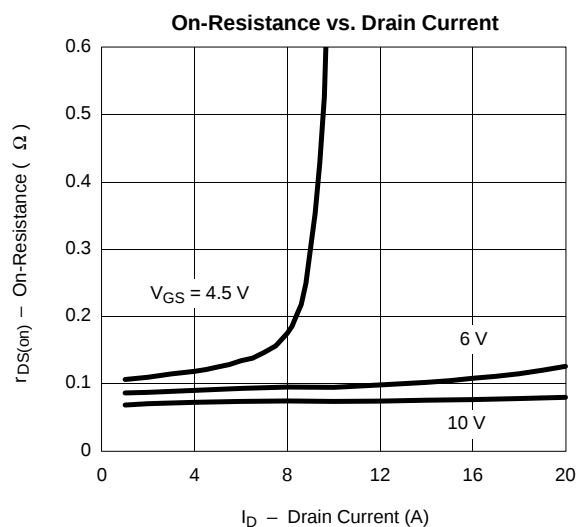
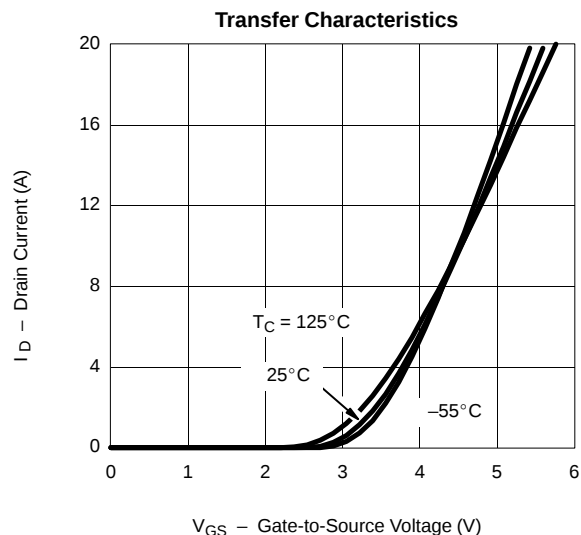
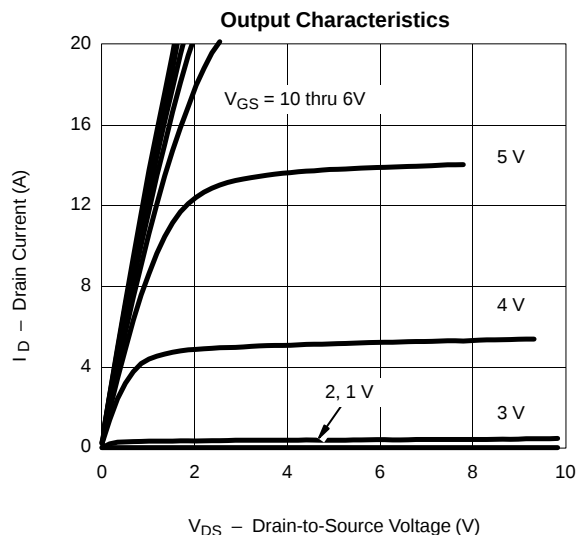
N-CHANNEL





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

P-CHANNEL



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

P-CHANNEL

